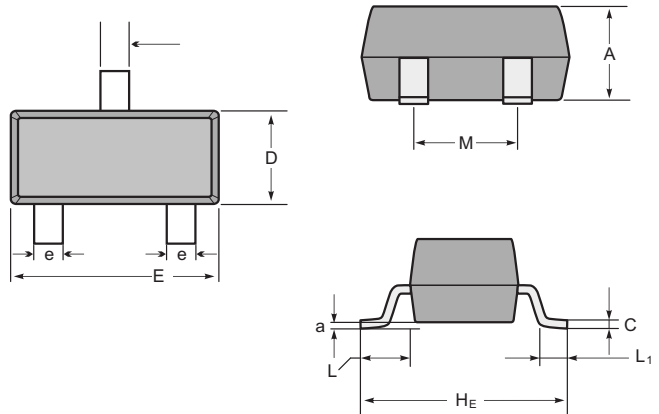
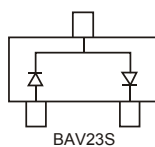
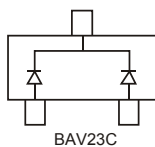
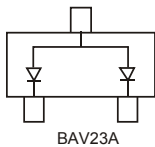


■ Features

- Fast Switching Speed
- For General Purpose Switching Applications.
- High Conductance



SOT-23 mechanical data

UNIT		A	C	D	E	H _E	e	M	L	L ₁	a
mm	max	1.1	0.15	1.4	3.0	2.6	0.5	1.95	0.55 (ref)	0.36 (ref)	0.0
	min	0.9	0.08	1.2	2.8	2.2	0.3	1.7			0.15
mil	max	43	6	55	118	102	20	77	22 (ref)	14 (ref)	0.0
	min	35	3	47	110	87	12	67			6

■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Reverse Voltage	V _{RRM}	250	V
Working Peak Reverse Voltage	V _{RWM}	200	
DC Blocking Voltage	V _R	200	
RMS Reverse Voltage	V _{R(RMS)}	141	
Forward Continuous Current (Notes 1)	I _{FM}	400	mA
Non-Repetitive Peak Forward Surge Current	I _{FSM}	9	A
		3	
		1.7	
Repetitive Peak Forward Surge Current	I _{FRM}	625	mA
Power Dissipation	P _d	350	mW
Thermal Resistance Junction to Ambient	R _{θJA}	357	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature range	T _{stg}	-65 to 150	

1. Double Diode Loaded in Parallel. For Single Diode or Double Diode Loaded in Series, the continuous forward current should be reduced by half.

BAV23A/C/S

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V_R	$I_R = 100 \mu A$	250			V
Forward voltage	V_F	$I_F = 100 \text{ mA}$			1	
		$I_F = 200 \text{ mA}$			1.25	
Reverse voltage leakage current	I_R	$V_R = 200 \text{ V}, T_J = 25^\circ C$			100	nA
		$V_R = 200 \text{ V}, T_J = 150^\circ C$			100	μA
Junction capacitance	C_j	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$			5	pF
Reverse recovery time	t_{rr}	$I_F = I_R = 30 \text{ mA}, I_{rr} = 0.1 \times I_R, R_L = 100 \Omega$			50	ns

■ Marking

NO.	BAV23A	BAV23C	BAV23S
Marking	KT7	KT6	KL31

RATING AND CHARACTERISTIC CURVES (BAV23A/C/S)

